

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Ge, *et al.* Docket No.: TSM03-0660  
Serial No.: 10/699,574 Art Unit: TBD  
Filed: October 31, 2003 Examiner: TBD  
For: Strained Silicon Structure

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Date of Deposit: February 23, 2004

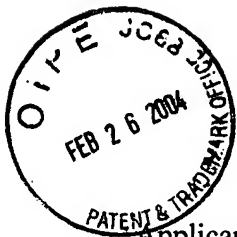
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PTO/SB/08A with 76 References Cited (5 pages)  
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Respectfully submitted,

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Ge, *et al.* Attorney Docket: TSM03-0660  
Filed: October 31, 2003 Examiner: TBD  
Serial No.: 10/699,574 Art Unit: 2811  
For: STRAINED SILICON STRUCTURE

Commissioner for Patents  
P. O. Box 1450  
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**INFORMATION DISCLOSURE STATEMENT**

The Applicant wishes to bring to the attention of the Patent and Trademark Office the information noted on the enclosed form PTO/SB/08A that may be considered material to the examination of the above-identified application.

No fee is due at this time, as this Information Disclosure Statement is being filed pursuant to 37 C.F.R. § 1.97(b)(3), before the mailing of a first Office action on the merits.

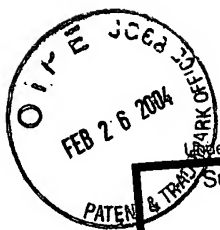
Cite numbers 1-45 are newly cited prior art being filed under the waived requirement of 37 CFR 1.98 (a)(2)(i) dated July 11, 2003, therefore, copies of these U.S. patents are not included.

Respectfully submitted,

2/23/2004  
Date

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PTO/SB/08A (05-03)

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Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

**Complete if Known**

Application Number	10/699,574
Filing Date	October 31, 2003
First Named Inventor	Ge, et al.
Art Unit	2811
Examiner Name	TBD
Attorney Docket Number	TSM03-0660

Sheet 1 of 5

**U.S. PATENT DOCUMENTS**

Examiner Initials*	Cite No.	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code <sup>2</sup> (if known)			
	1	US-4,072,974	02-07-1978	Ipri	
	2	US-4,631,803	12-30-1986	Hunter, et al.	
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	4	US-5,024,723	06-18-1991	Goesele, et al.	
	5	US-5,213,986	05-25-1993	Pinker, et al.	
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				Application Number	10/699,574
				Filing Date	October 31, 2003
				First Named Inventor	Ge, <i>et al.</i>
				Art Unit	2811
				Examiner Name	TBD
Sheet	2	of	5	Attorney Docket Number	TSM03-0660

[illegible]

FOREIGN PATENT DOCUMENTS					
Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
	Country Code <sup>3</sup> - Number <sup>4</sup> - Kind Code <sup>5</sup> ( <i>if known</i> )				
46	WO 03/017336 A2	02-27-2003	Amberwave Systems Corporation		

Examiner Signature		Date Considered	
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				Examiner Name	TBD
Sheet	3	of	5	Attorney Docket Number	TSM03-0660

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
	47	ISMAIL, K., <i>et al.</i> , "Electron Transport Properties of Si/SiGe Heterostructures: Measurements and Device Implications," Applied Physics Letter, Vol. 63, No. 5, (August 2, 1993), pp. 660-662.	
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Sheet	4	of	5	Attorney Docket Number	TSM03-0660

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
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	60	MATTHEWS, J.W., <i>et al.</i> , "Defects in Epitaxial Multilayers – III. Preparation of Almost Perfect Multilayers," Journal of Crystal Growth, Vol. 32, (1976), pp. 265-273.	
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Examiner Signature	Date Considered
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